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Table of Contents

Preface

Chapter I - Device Engineering and Memory Technology

Towards Efficient Neural Networks On-A-Chip: Joint Hardware-Algorithm Approaches (1-31) 1
Xiaocong Du[1], Gokul Krishnan[1], Abinash Mohanty[1], Zheng Li[2], Gouranga Charan[1] and Yu Cao[1]
[1]School of ECEE, Arizona State University, Tempe, Arizona, USA
[2]School of CIDSE, Arizona State University, Tempe, Arizona, USA

Efficient Weight Mapping Scheme without Verification for RRAM Based Neuromorphic Computing (1-8) 6
Shuanglin Zhang, Huaqiang Wu, Bin Gao and He Qian
Institute of Microelectronics, Tsinghua University, Beijing, China

Investigation on LDMOS Characteristics of Layout Dependence in FinFET Technology (1-11) 9
Gang Wang, Byunghak Lee, Guiying Ma, Nan Wang, Mike Tang, Kellin Ding, Breeze Zhou and Jianhua Ju
Semiconductor Manufacturing International (Shanghai) Corporation, Shanghai, China

A Novel 500-700V Ultra High-Voltage LDMOS with Low On-State Resistance by Multiple Local RESURF Enhancement Technology (1-76) 12
Mao Li, DeYan Chen, Dae-Sub Jung and XueJie Shi
Semiconductor Manufacturing International (Shanghai) Corporation, Shanghai, China

New Understanding of Negative Capacitance Devices for Low-Power Logic Applications* (1-84) 15
Qianqian Huang, Huimin Wang, Yang Zhao, Mengxuan Yang, Zhongxin Liang, Kunkun Zhu and Ru Huang
Key Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronics, Peking University, Beijing, China
National Key Laboratory of Science and Technology on Micro/Nano Fabrication, Beijing, China

Investigation of Negative Capacitance Effect from Domain Switching Dynamics (1-83) 18
Kunkun Zhu[1,2], Qianqian Huang[2], Huimin Wang[2], Mengxuan Yang[2] , Yang Zhao[2], Zhongxin Liang[2], Hao Pan[3], Jing Ma[3] and Ru Huang[2]
[1]Shenzhen Graduate School, Peking University, Shenzhen, China
[2]Key Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronics, Peking University, Beijing, China
[3]Department of Materials Science and Engineering, Tsinghua University, Beijing, China

Accelerating Deep Neural Networks with Analog Memory Devices (1-1)** 21
G.W. Burr, S. Ambrogio, P. Narayanan, H. Tsai, C.S. Mackin and A. Chen

IBM Research, Almaden, San Jose, California, USA

The Impact of Interconnect Resistance on One-Selector One-Resistor (1S1R) Crossbar Array Performance (1-39) 24
Yujia Li[1, 2], Bin Gao[1], Huaqiang Wu[1], Wanrong Zhang[2] and He Qian[1]
[1]*Institute of Microelectronics, Tsinghua University, Beijing, China*
[2]*Faculty of Information Technology, Beijing University of Technology, Beijing, China*

Effect of Different Top Electrodes on Performance of Low-Power Flexible RRAM Based on Te/HfO_2/TiN Cell (1-48) 27
Jingwei Zhang, Fang Wang, Jiaqiang Shen, Wenxi Li, Zhengchun Yang and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, China

Fast Development of High-performance ICs in AI/IoT Era* (1-5) 30
Min-hwa Chi and Richard Chang
SiEn (QinDao) Integrated Circuits Co., ShanDong, China

Defect Assessment in AlN Nucleation Layers Grown on Silicon and Silicon-on-Insulator Substrates* (1-4) 34
E. Simoen[1,2], W. Zhang[3], J. Zhang[3], C. Claeys[4] and M. Zhao[1]
[1]*Imec, Leuven, Belgium*
[2]*Depart. Solid State Sciences, Ghent University, Gent, Belgium*
[3]*School of Microelectronics, Xidian University, Xi'an, China*
[4]*Electr. Eng. Depart., KU Leuven, Leuven, Belgium*

Flicker Noise Simulation By Physical Trap Model (1-74) 37
YiYu Chen, YongSheng Yang and XueJie Shi
Semiconductor Manufacturing International (Shanghai) Corporation, Shanghai, China

Simulation of Low-Pass Filter Circuit Based on TiOx-Based Memristive Device (1-50) 40
Jingsi Sun, Yupeng Xing, Fang Wang, Wenxi Li, Kai Hu and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

RFFE Integration Design for 5G in 0.13um RFSOI Technology (1-40) 43
Ruofan Dai, Jiangchuan Ren, Jun He, Jun Xiao and Weiran Kong
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Die Attachment Material Based on Micro Ag Paste for the Application of High Powder Devices (1-67) 46
Jinting Jiu, Tetsu Takemasa, Junko Seino and Yoshie Tachibana
Senju metal Industry Co., Ltd. Japan

Optimization of RF Performance and Reliability of 28V RF-LDMOS (1-3) 51
Ying Cai[1], Zhengliang Zhou[1], Haifeng Mo[2], Hu Peng[2] , Yaohui Zhang[2], Jiye Yang[1], Jingfeng Huang[1], Han Yu[1] and Junlang Li[1]
[1]*Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China*
[2]*System Integration and IC Design Division Suzhou, Institute of Nano-Tech and Nano-Bionics (SINANO), CAS, Suzhou, China*

Impact of Annealing Temperature on Performance Enhancement for Charge Trapping Memory with $(HfO_2)_{0.9}(Al_2O_3)_{0.1}$ Trapping Layer (1-6) 54

Zhaozhao Hou[1,2], Jiaxin Yao[1,2], Jie Gu[1,2], Zhenhua Wu[1] and Huaxiang Yin[1,2]
[1]Key Laboratory of Microelectronics Devices and Integrated Technology, Institute of Microelectronics of Chinese Academy of Sciences, Beijing, China
[2]University of Chinese Academy of Sciences, Beijing, China

Thickness-Dominated Forming Conditions of TaO_x-Based Memristor (1-7) **57**
Chuang Li, Fang Wang, Wenxi Li, Jingwei Zhang, Jinshi Zhao and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

Comprehensive Investigation of Flat-band Voltage Modulation by High-k NPT for Advanced HKMG Technology (1-9) **60**
Jiaxin Yao[1,2], Zhaozhao Hou[1,2], Wenjuan Xiong[1], Qingzhu Zhang[1], Zhenhua Wu[1] and Huaxiang Yin[1,2]
[1]Key Laboratory of Microelectronics Devices and Integrated Technology, Institute of Microelectronics of Chinese Academy of Sciences, Beijing, China
[2]University of Chinese Academy of Sciences, Beijing, China

A Method to Improve SST Flash Cell Program Function (1-10) **63**
Chong Huang, Peizhong Zhang, Haiyan Qin and Yang Zhou
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Conductance Quantization in Oxide-Based Resistive Switching Device (1-12) **66**
Qingxi Duan, Jingxian Li, Jiadi Zhu, Teng Zhang, Jingjing Yang, Yuchao Yang and Ru Huang
Key Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronics, Peking University, Beijing, China

Thickness Dependence Characteristics of High-κ Al_2O_3 Based Metal-Insulator-Metal Antifuse (1-13) **69**
Min Tian and Huicai Zhong
Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China
University of Chinese Academy of Sciences, Beijing, China

A High Efficiency N-Channel Single Poly OTP Cell Structure in Standard CMOS Process (1-14) **72**
Yu Chen, Yuan Yuan, Hualun Chen and Yuhua Zhang
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Improvement of Cell's Performance for Low Power Self-Aligned Split-Gate SONOS Memory Device (1-15) **75**
Jun Hu[2], Zhaozhao Xu[1,2], Kegang Zhang[2], Wei Xiong[2], Donghua Liu[2], Hualun Chen[2] and Wensheng Qian[2]
[1]State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, Shanghai, China
[2]ShanghaiHuahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Study of 7V Device Application Based on 0.18um Platform Process (1-16) **79**
Jun Hu, Jike Wu, Xiuliang Cao and Wensheng Qian

HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China

A Study of LDMOS BV Improvement by Gate Architecture Optimization (1-17) **82**
Ziquan Fang[1], Zhaozhao Xu[1,2] and Wensheng Qian[1]
[1]HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China
[2]State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, Shanghai, China

Study of Drive-Current Enhancement and Field Plate Optimization in 500V High-Voltage NLDMOS (1-18) **85**
Wenting Duan, Donghua Liu and Wensheng Qian
HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Benefits of Nitrogen Co-Implantation on 28nm SRAM (1-19) **88**
Fan Qin, Zhou Xiaojun and Liu Wei
Huali Microelectronics Corporation, Shanghai, China

Study of Ultra High Voltage 500V NLDMOS with Aggressive Design of Drift Region (1-20) **91**
Wenting Duan[1], Chunyu Yuan[1], Zhaozhao Xu[1,2], Wensheng Qian[1] and Donghua Liu[1]
[1]HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China
[2]State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, Shanghai, China

Study on the Data Trend of Pitch Line With Pupilgram (1-21) **95**
Xie Weimei, Guo Lianfeng and Yu Shirui
Huali Microelectronics Corporation,Shanghai, China

Significant Improvement of UTS CIS SRAM V_{min} Yield by Optimizing LDD Implantation (1-24) **98**
Weiwei Ma, Chao Sun and Yamin Cao
Huali Integrated Circuit Corporation, Shanghai, China

A Novel Method for STI Top Corner Rounding by Etch Process to Improve Leakage and SRAM Performance (1-25) **101**
Lin Gu
Huali Microelectronics Corporation,Shanghai, China

An Effective Method to Reduce Bump Defect is Investigated (1-26) **104**
Xiang Guangxin, Gong Yiqi, Wei Xiang, Luo Zhigang, Bao Yu, Zhou Haifeng, Fang Jingxun and Albert Pang
Huali Microelectronics Corporation,Shanghai, China

A Study of Inductor and its Model in SiGe BICMOS Process (1-27) **107**
Zhang Jian and Donghua Liu
HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Improved Ge Doped Cap Layer for Embedded SiGe Epitaxial Growth in 28 nm CMOS Technology (1-28) **111**

Tanjun, Chenyongyue, Huangqiumin, Hongjiaqi, Yanqiang, Zhouhaifeng and Fangjingxun
Huali Microelectronics Corporation, Shanghai, China

Optimization of Metal Hard Mask Tin for Tiny Particle Reduction (1-29) **114**
Li Xixiang, Bao Yu, Wang Xiaofang, Cao Yanpeng, Zeng Zhaoqin and Zhou Haifeng
Huali Microelectronics Corporation, Shanghai, China

Improved Endurance of SONOS Cell by Smart Poly Recessed Method (1-41) **117**
Hualun Chen, Yuanyuan Shan and Yu Chen
Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Improved Data Retention of Single Gate PMOS OTP Cell by Dielectric Film Process Optimization (1-42) **120**
Hualun Chen, Yuan Yuan, Yu Chen and Yuhua Zhang
Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Investigation of Quantum-Dot Characteristic Based on Different Bulk Silicon FinFET Device Models (1-43) **122**
Jie Gu[1,2], Zhaozhao Hou[1,2], Jiaxin Yao[1,2], Zhenhua Wu[1] and Huaxiang Yin[1,2]
[1]*Key Laboratory of Microelectronics Devices and Integrated Technology, Institute of Microelectronics of Chinese Academy of Sciences, Beijing, China*
[2]*University of Chinese Academy of Sciences, Beijing, China*

Nanometer-Thin Pure B Layers Grown by MBE as Metal Diffusion Barrier on GaN Diodes (1-44) **125**
Shivakumar D. Thammaiah[1,3], John Lundsgaard Hansen[2] and Lis K. Nanver[1,3]
[1]*Department of Materials and Production, Aalborg University, Aalborg, Denmark*
[2]*Interdisciplinary Nanoscience Center(iNANO), Aarhus University, Aarhus, Denmark*
[3]*MESA+ Institute for Nanotechnology, University of Twente, Enschede, The Netherlands*

EFA Method of AA-Bridge-Type-Defect of SONOS NOR Flash (1-47) **128**
Qingwen Zhang, Zhimin Zeng, Yuxiang Zhang, Yuan Wu and Chenjie Zhou
Huahong Grace Semiconductor Manufacture Corporation, Shanghai, China

Performance Optimization of HfO_x-Based Transparent Resistance Random Access Memory (1-51) **132**
Jinrong Huang, Fang Wang, Luguang Wang, Wei Mi, Baozen Zhou and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

SRAM Standby Current Fail Analysis using OBIRCH, Voltage Contrast and Junction Stain (1-52) **135**
Jinjin Xie, Xiangbai Ma and Zhimin Zeng
Huahong Grace Semiconductor Manufacture Corporation, Shanghai, China

High Performance NLDMOS with Optimized Channel and Drift (1-57) **139**
Wensheng Qian[1], Zhaozhao Xu[1,2] and Ziquan Fang[1]
[1]*HuaHong Grace Semiconductor Manufacturing Corporation, Shanghai, China*
[2]*State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, Shanghai, China*

Impact of Forming Voltage Polarity on HfO_2-based RRAM Performance (1-58) 142
Jian Kang[1], Zongwei Wang[1], Yishao Chen[1], Yichen Fang[1], Qilin Zheng[1], Yuchao Yang[1], Jintong Xu[2], Yimao Cai[1] and Ru Huang[1]
[1]Key Laboratory of Microelectronic Devices and Circuits, Institute of Microelectronics, Peking University, Beijing, China
[2]Key Laboratory of Infrared Imaging Materials and Detectors, Shanghai Institute of Technical Physics, Chinese Academy of Science

Optimization of Passivation and Top Metal Layer Crack in Temperature Cycle Test of RF-LDMOS (1-59) 145
Ying Cai, Jingfeng Huang and Han Yu
Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Product Design Optimization for Prevent Bias Highly Accelerated Stress Failure of RF-LDMOS (1-60) 148
Han Yu, Jingfeng Huang and Ying Cai
Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

The GSG-Pad Layout Optimization for Test-Key of mm-Wave Devices (1-61) 151
Quan Wang, Linlin Liu, Yueyi Feng, Wei Zhou, Ao Guo, Hongbo Ye and Yingjia Guo
Shanghai IC R&D Center Co., Ltd ,Zhangjiang HighTech Park, Shanghai, China

On-Resistance Improvement Impacted by Trapping Effects in Fin-LDMOS Technology (1-63) 155
Gang Wang, Byunghak Lee, Guiying Ma, Nan Wang and Kellin Ding
Semiconductor Manufacturing International Corporation (SMIC), Shanghai, China

Improvement of SPAD Photon Detection Efficiency with Diffraction Window Layer (1-69) 158
Feiyang Sun[1], Zhong Wu[1], Sihui Zhu[1] and Yue Xu[1,2]
[1]College of electronic and optical engineering & College of microelectronics in Nanjing University of Posts and Telecommunications, Nanjing, China
[2]National and Local Joint Engineering Laboratory of RF Integration and Micro-assembly Technology, Nanjing, China

The Effects of Carbon on Phosphorus Diffusion and Activation in Ge (1-78) 161
Xiangyang Hu, Bingxin Zhang, Xiaoyan Xu, Ming Li, Xia An and Ru Huang
Key Laboratory of Microelectronic Devices and Circuits, Institute of Microelectronics, Peking University, China

Optimal V_{DD} Assessment of CMOS Technology Considering Circuit Reliability Tradeoffs (1-79) 164
Minghao Liu, Shaofeng Guo, Runsheng Wang and Ru Huang
Institute of Microelectronics, Peking University Beijing, China

A High-Performance Source-Pocket Tunnel Field-Effect Transistor (1-81) 167
Gaobo Xu, Huaxiang Yin, Qiuxia Xu, Guilong Tao, Zhenhua Wu, Jianhui Bo, Jinshun Bi, Yongliang Li, Huajie Zhou, Haiping Shang, Jinbiao Liu, Junjie Li, Wenjuan Xiong, Junfeng Li, Huilong Zhu, Chao Zhao and Wenwu Wang
Key Laboratory of Microelectronics Devices & Integrated Technology, Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China

The Investigation of Source Doping Effect on On-state Current in Homojunction and Heterojunction Tunneling FETs (1-85) 170
Shuang Xia, Qian Xie, Mingjun Liu and Zheng Wang
University of Electronic Science and Technology of China, Chengdu, China

Single-Ended Sub-Threshold 9T SRAM Cell with Ground Cut-Off (1-86) 174
Smaran Adarsh, M. Tanmay and M.S. Sunita
Dept. Electronics and Communication, PES University, Bangalore, India

Improved Endurance of SONOS Flash Cells by Facile Lithography Processing Adjustment (1-88) 177
Ning Wang, Wei Xiong, Kegang Zhang, Hualun Chen and Pingsheng Zhou
Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Local Layout Effect Impact to Single Device in SRAM 6T Cell (1-91) 180
Yijun Zhang, Nan Wang, Yu Li, Yuan Wang, Xiaohua Li, Guiying Ma, Yongcheng Zhai and Jianhua Ju
Semiconductor Manufacturing International Corporation (SMIC), Shanghai, China

SiGe Layers Defect of 28nm Node PMOSFETS in Advanced CMOS Technology (1-30) 184
Qiuming Huang, Yongyue Chen, Jiaqi Hong, Qiang Yan, Jun Tan and Haifeng Zhou
Shanghai Huali Microelectronics Corporation, Shanghai, China

Chapter II – Lithography and Patterning

Semi-Implicit Mask Synthesis with Additive Operator Splitting (2-3) 187
Yijiang Shen and Fei Peng
School of Automation, Guangdong University of Technology, Guangzhou, China

EUV Mask Near-Field Synthesis* (2-27) 190
Taian Fan[1], Xu Ma[3], Yayi Wei[1,2] and Lisong Dong[1]
[1]Institute of Microelectronics of Chinese Academy of Sciences, Integrated Circuit Advanced Process Center & Key Laboratory of Microelectronics Devices & Integrated Technology, Beijing, China
[2]University of Chinese Academy of Sciences, School of Microelectronics, Beijing, China
[3]Key Laboratory of Photoelectronic Imaging Technology and System of Ministry of Education of China, School of Optoelectronics, Beijing Institute of Technology, China

Design Driven Test Patterns for SMO OPC and SPA (2-20)
Le Ma[1], Yingli Duan[2], Lisong Dong[1], Libin Zhang[1] and Yayi Wei[1,3] 194
[1]Integrated Circuit Advanced Process Center, Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China
[2]Gangzheng Intellectual Property Center Co. Ltd, Beijing, China
[3]University of Chinese Academy of Sciences, Beijing, China

Effective Mask Patterning Strategy as Design Complexity and CD Stability 197
Young Ham, Yohan Choi, Michael Green, Mohamed Ramadan and Chris Progler

Photronics, Inc, Boise, Idaho, USA

Novel Gap Filling BARC with High Chemical Resistance* (2-2) **200**
Yuto Hashimoto, Shigetaka Otagiri, Hiroto Ogata, Satoshi Kamibayashi, Takafumi Endo, Yuki Endo and Takahiro Kishioka
Semiconductor Materials Research Department, Material Research Laboratories, Nissan Chemical Corporation, Toyama, Japan

High Volume Semiconductor Manufacturing using Nanoimprint Lithography*(2-25) **203**
Keita Sakai
Semiconductor Production Equipment PLM Center 3, Canon Inc., Utsunomiya, Japan

The Monitor Strategies of Lens Flare for Nikon ArF And KrF Scanner Machines: Simulated Results and Discussion (2-13) **206**
Zhe Zheng[1], Zhenyu Yang[1], Chun Shao[1] and Junji Ikeda[2]
[1]Nikon Precision Shanghai Co., Ltd., Pudong New District, Shanghai, China
[2]Nikon Corporation, 201-9, Miizugahara, Kumagaya, Saitama, Japan

The Impact of Segment Length on the Process Window in SMO (2-22) **209**
Yonghua Zhang[1,2], Lisong Dong[1], Yayi Wei[1] and Haoru Hu[1,2]
[1]Integrated Circuit Advanced Process Center, Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China
[2]College of Big Date and Information Engineering, Guizhou University, Guiyang, China

Prediction Model of Etching Bias Based on Artificial Neural Network (2-23) **212**
Haoru Hu[1,2], Lisong Dong[1], Yayi Wei[1] and Yonghua Zhang[1,2]
[1]Integrated Circuit Advanced Process Center, Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China
[2]College of Data and Information Engineering Guizhou University, Guiyang, China

Mask and Template Assignment on DSA-MP with Triple BCP Materials Lithography (2-26) **215**
Cong Cao[1], Xingquan Li[2], Jianli Chen[1] and Wenxing Zhu[1]
[1]Center for Discrete Mathematics and Theoretical Computer Science, Fuzhou University, Fuzhou, China
[2]School of Mathematics and Statistics, Minnan Normal University, Zhangzhou, China

The Study of Mask Crosstalk Defects from Developer and Etching (2-28) **218**
Heng-Jen Lee, Yuan Hsu, Jackie Cheng, Mei-Yu Liu, Colbert Lu and Tomas Chin
Photronics DNP Mask Corp., R&D Division, PDMC, Hsin-Chu City, Taiwan

Methodology for Building MPC Model for Advanced Lithography Nodes (2-30) **221**
Mohamed Ramadan[1], Brian Dillon[2], Michael Green[1], Young Ham[1] and Chris Progler[1]
[1]Photronics Inc., Boise, USA
[2]Nippon Control System Corporation, Tokyo, Japan

Exposure System Improvement for Greater Productivity (2-44) **224**
Takahiro Takiguchi, Kenta Kita, Yosuke Takarada, Ryo Kasai, Satoru Sugiyama and Tsuneari Fukada
Optical Products Operations, Canon Inc, Utsunomiya, Japan

65nm Node Possibility Study in 200 mm Fabs (2-9) **227**
Weifeng Li, Huiping Shen, Yili Gu and Lei Wang
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Chapter III – Dry & Wet Etch and Cleaning

Estimating the Etching Depth Limit in Deep Silicon Etching (3-18) **230**
Yuanhe Zhao[1] and Yuanwei Lin[2]
[1]*School of Pharmaceutical Sciences, Peking University, Beijing, China*
[2]*Department of Semiconductor Etching, NAURA Technology Group Co., Ltd., Beijing, China*

Advanced Si Etch System for 14nm and Beyond* (3-43) **234**
Tomoki Suemasa, Guodong Chen, Zhongwei Jiang and Yahui Huang
NAURA Microelectronics Equipment Co., Ltd, Beijing, China

A Study of Deep Silicon Etching for Power Device Fabrication (3-32) **239**
Wan Yu, Wang Chun, Zhang Yunge, Qiu Chunlong, Zheng Youshan and Li Dongsan
NAURA Technology Group Co., Ltd., Beijing, China

Cryogenic Nano-Aerosol: Particle Removal and Damage-Free Cleaning For IC Manufacturing (3-2) **243**
Jeffrey M. Lauerhaas[1], Gregory P. Thomes[1], Brent D. Schwab[1], Christina Ann Rathman[1], Antonio L. P. Rotondaro[2], Derek W. Bassett[2], Jeffery W. Butterbaugh[1] and Chimaobi Mbanaso[1]
[1]*TEL FSI, Inc., Chaska, MN, USA*
[2]*Tokyo Electron America, Inc., Austin, TX, USA*

Inductive Coupled Downstream Plasma CD Trim Process Stability Study (3-13) **246**
Yali Fu[1,2], Shawming Ma[3], Yi Wang[1], Linda Sui[2], Lu Chen[2], Vijay Vaniapura[3], Li Diao[3], Mingjie Jiao[2], Hongwei Chen[2]
[1]*Peking University, School of software and microelectronics, Beijing, China*
[2]*Mattson Technology, China Field Process Engineering, Beijing, China*
[3]*Mattson Technology, Inc, Fremont, CA, USA*

Selective Plasma Etching of Silicon Nitride over Silicon Dioxide by Tuning Helium (3-1) **N/A**
Ke Liu[1], Li Qi[1], Zhongwei Jiang[1], Xiaoyang Cheng[1], Yahui Huang[1] , Ling Liang[2], Haibo Xie[2] and Zuixin Zeng[2]
[1]*Beijing NAURA Microelectronics Equipment Co., Ltd, Beijing, China*
[2]*Yangtze Memory Technologies Co., Ltd, Wuhan, China*

Reactive-Ion Etching of Cr-Doped Sb_2Te_3 Thin Film in SF_6/O_2 Plasma for Non-Volatile Phase-Change Memories (3-17) **249**
Luguang Wang, Fang Wang, Yuxiang Li, Jinrong Huang, Wei Li and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

Silicon OLED Microdisplay Metal Mask Cleaning Technology Research (3-47) **N/A**
Yang Zhuo

SEVEVSTAR SEMICONDUCTOR TECHNOLOGISE CO.,LTD, Beijing, China

Study of Photoresist Plug Etching Back with CO/O_2 Plasma for Dense-ISO Via Recess Loading Tunning (3-9) 252
Xiaobing Liu, Manson Huang, Michael Tsai, Zhaoxiang Wang and Xingcai Su
Advanced Micro-Fabrication Equipment Inc, Shanghai, China

Study on Wafer De-Chuck for High Aspect Ratio Etch Process (3-14) 255
Guorong Li[1,2], Zhiqiang Liu[2], Michael Tsai[2], Zhaoxiang Wang[2], Ping Liu[2] and Xing Zhang[1]
[1]School of Software and Microelectronics, Peking University, Beijing, China
[2]Advanced Micro-Fabrication Equipment Inc. (AMEC), Shanghai, China

Tunable Silicon-Germanium and Silicon Selective Etch in 5-Nanometer and Below Applications (3-16) 258
Chien-Pin Sherman Hsu
Avantor , Chu-Bei, Hsinchu, Taiwan

Optimize of High-k Capping Layer Loss Thickness in DPRM Process to Avoid V_{th} Shift (3-23) 260
Meng Shi[1], Cheng Liu[1], Haitao Yan[3], Haiyang Mao[2], Baodong Han[3] and Guangmei Xia[3]
[1]School of Microelectronics, University of Chinese Academy of Sciences (UCAS), Beijing, China
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[3]Semiconductor Manufacturing International Corporation (SMIC), Beijing, China

Chapter IV – Thin Film, Plating and Process Integration

Cobalt Electrofill for Future Generations of Contacts and Interconnects* (4-2) 263
Tighe A. Spurlin, Matthew A. Rigsby, Lee Brogan, Natalia Doubina, Yihua Liu, Edward Opocensky, Jian Zhou and Jonathan Reid
Lam Research, Tualatin, Oregon, USA

Difficulty Involved to Observe the Surface Smoothing Effect of an Amorphous High-k Dielectric Thin Film Deposited by Atomic Layer Deposition on a Metastable Metal Film (4-37) 266
W.S. Lau[1], L. Du[1], H. Wong[2] and S. Dong[1]
[1]Zhejiang University, Department of Information Science and Electronic Engineering, Hangzhou, China
[2]City University of Hong Kong, Department of Electronic Engineering, Kowloon, Hong Kong

Surface Smoothing And Roughening Effects of High-k Dielectric Materials Deposited by Atomic Layer Deposition and Their Significance for MIM Capacitors Used in DRAM Technology (4-4) 269
W.S. Lau
Zhejiang University, Department of Information Science and Electronic Engineering, Hangzhou, China

An Efficient Method of Wafer Thermal Uniformity Improvement and Wafer Edge Yield Enhancement by Utilizing Backside Film Removing (4-13) 272

Zhejun Liu, Peng Wang, Ran Huang, Ying Xu and Wei Zhou
Shanghai Huali Integrated Circuit Corporation, Shanghai, China

Detect, Understand and Fix Starburst Defect at Via Litho Film Stacks (4-8) **275**
Zhiguo Sun, Eswar Ramanathan, Mary Claire Silvestre, Tingge Xu, Kripa Chauhan, Vijaya Rana, Joseph Shepard Jr, Vijayalakshmi Seshachalam, Minrui Wang, Anbu Selvam KM Mahalingam and Yang Bum Lee
Globalfoundries, Malta, New York, USA

Press-Fit Whisker and its Growth Contributing Factors-Part I (4-15) **278**
Flora He[1], Shuzhao Cao[2], Dennis Chan[1], Crystal Li[1], Geoffrey Tong[1], Dennis Yee[1], Xi Cao[2], and John Lehman[3]
[1]Research & Development, Interconnect Technology, Dow Electronic Materials, Hong Kong, China
[2]Process Department, Huawei Technologies Co. Ltd., Shenzhen, China
[3]Engineering Department, Amphenol ICC, Nashua, NH, USA

The Effect of TiN Cap Layer Thickness and N_2 Flow on Threshold Voltage and Resistance in High-k Metal Gate Integration (4-28) **N/A**
Cheng Liu[1], Meng Shi[1], Jianqiang Liu[2], Zirui Liu[2], Aiji Wang[2], Feng Shi[2] and Haiyang Mao[3]
[1]School of Microelectronics, University of Chinese Academy of Sciences, Beijing, China
[2]Semiconductor Manufacturing North China Corporation (SMNC), China
[3]Smart Sensing R&D Center, Institute of Microelectronics of Chinese Academy of Sciences, Beijing, China

Brief Introduction of Thermal Oxidation Technology (4-32) **282**
Yan Sun, Yanhua Wu, Kexue Liu and Wenfei Zhou
Beijing NAURA Microelectronics Equipment Co., Ltd., Beijing, China

The Study of Relation Between Temperature Distribution on Silicon Wafer with Gas Flow Rate and Temperature Ramp Rate (4-38) **285**
Kexue Liu, Yanhua Wu, Yan Sun, Yuanzhi Li and Wenfei Zhou
Beijing NAURA Microelectronics Equipment Co., Ltd., Beijing, China

Properties of PVD AlN for LED Applications (4-7) **288**
Bingliang Guo, Boyu Dong, Xuewei Wu, Xinying Li, Shubo Wu, Yilong Yang, Yujie Liu, Jiahao Zhang, Lu Zhang, Yujing Chen, Chenguang Zhao, Yinggong Ma, Xiaoping Shi, Hougong Wang and Peijun Ding
Beijing NAURA Microelectronics Equipment Co., Ltd., Beijing, China

Synthesis of WSe_2 by Chemical Vapor Deposition and Influence of Hydrogen on Morphology (4-16) **291**
Xichao Di, Fang Wang, Junqing Wei, Baojun Zhang, Xin Lin and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, China

Improved Crystal Quality of C-Axis Oriented AlN Films with ZnO Buffer Layer (4-17) **294**
Shuo Yan, Fang Wang, Kaifei Dong, Meng Deng, Yujie Yuan, Yinping Miao and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

A New Differential Pressure Sensor Based Mass Flow Controller for Advanced Semiconductor Processing (4-5) 297
Alexandra Liso, Anthony Kehoe and Mohamed Saleem
Brooks Instrument, Hatfield, PA, USA

Comprehensive Study of Interfacial Charges in the GeO_x/Al_2O_3 Gate Stack of Ge by Ozone Oxidation (4-31) 302
Lixing Zhou[1,2], Xiaolei Wang[1], Jinjuan Xiang[1], Chao Zhao[1,2], Tianchun Ye[1,2] and Wenwu Wang[1,2]
[1]Key Laboratory of Microelectronics Devices & Integrated Technology, Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China
[2]University of Chinese Academy of Sciences, Beijing, China

Plasma Process Optimization of Silicon Film Deposition from Trichlorosiliane Precursor with OES Monitoring (4-29) 305
Chien-Chieh Lee[1], Song-Ho Wang[2], Hsueh-Er Chang[2], Yiin-Kuen Fuh[2], Tomi T. Li[2], Ya-Hui Chiou[3] and Hsin-Chuan Cheng[3]
[1]Optical Science Center, National Central University, Taoyuan City, Taiwan
[2]Department of Mechanical Engineering, National Central University, Taoyuan City, Taiwan
[3]Shihlien Fine Chemicals Co., Ltd. Taoyuan City, Taiwan

Study of Spacer Formation in FDSOI Technology (4-1) 309
Yang Song, Kang Ye and Changfeng Wang
Huali Microelectronics Corporation, Shanghai, China

Integrated Circuit Back End of Line Defect Detection (4-12) 311
Wang Wei, Zhu Zhenhua, Zhang Chao, Bei Duohui and Yang Ming
Semiconductor Manufacturing International Corporation, Shanghai, China

Fabrication of Flexible Surface Acoustic Wave Devices Based on Aluminium Nitride (4-18) 315
Meng Deng, Fang Wang, Kaifei Dong, Dianyou Song, Shuo Yan and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

Chapter V – CMP and Post-Polish Cleaning

Study and Improvement on Tungsten Recess in CMP Process* (5-46) 318
Lei Zhang, Yefang Zhu and Jingxun Fang
Technology Development, Shanghai Huali Microelectronics Corporation, Shanghai, China

Optimization on Chemical Mechanical Planarization of Chromium Doped Antimony Telluride (Cr-SbTe) for PCM Devices (5-36) 321
Luguang Wang, Fang Wang, Yuxiang Li, Jinrong Huang, Wei Li and Kailiang Zhang
Tianjin Key Laboratory of Film Electronic & Communication Devices, School of Electrical & Electronic Engineering, Tianjin University of Technology, Tianjin, China

Within Wafer & Wafer to Wafer Thickness Uniformity Controllable Study on ILD- 324

CMP Via Polishing Pad's Physical Property Analysis and Linear Interval Feedback APC's Implementation (5-37)
Zhijie Zhang and Hongdi Wang
Semiconductor Manufacturing North China (Beijing) Corp, Beijing, China

High Rate Ceria Slurry and Pad Combo Solution for Bulk Oxide CMP* (5-14) **327**
Jinfeng Wang, Atsushi Umeda, Chen Chih Tsai and Chul Woo Nam
Cabot Microelectronics Corporation, Aurora, Illinois, USA

A New Nanoparticle Characterization Technology for CMP Slurries (5-9) **330**
Siqin He[1], Derek Oberreit[1], Gary Van Schooneveld[2] and David Blackford[1]
[1]*Kanomax FMT, Inc., White Bear Lake, Minnesota, USA*
[2]*CT Associates, Inc., Eden Prairie, Minnesota, USA*

Effect of Wafer Wettability on Marangoni Drying Performance in Post–CMP Cleaning* (5-38) **333**
Changkun Li, Bingquan Wang, Dewen Zhao and Xinchun Lu
Department of Mechanical Engineering, Tsinghua University, Beijing, China

Study on Different Surfactants for Post CMP Cleaning of Novel Barrier (5-41) **336**
Siyu Tian[1,2], Baimei Tan[1,2], Qi Wang[1,2], Chunyu Han[1,2], Liu Yang[1,2] and Baohong Gao[1,2]
[1]*School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China*
[2]*Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China*

Effect of Ammonium Ion on Chemical Mechanical Polishing of Ru (5-27) **339**
Ziyan Wang[1,2], Jianwei Zhou[1,2], Chenwei Wang[1,2], Jiajie Zhang[1,2] and Qingwei Wang[1,2]
[1]*Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China*
[2]*School of Electronic Information Engineering, Hebei University of Technology,Tianjin, China*

Effect of BTA Derivative on Reduction of Galvanic Corrosion Between of Ru and Cu During CMP (5-42) **342**
JiaJie Zhang[1,2], Jianwei Zhou[1,2], Chenwei Wang[1,2], Ziyan Wang[1,2] and Qingwei Wang[1,2]
[1]*Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China*
[2]*School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China*

Effect of TT-LYK as the Inhibitor on Step Height Reduction for Copper CMP (5-15) **345**
Jiakai Zhou[1,2], Xinhuan Niu[1,2], Jianchao Wang[1,2], Kai Zhang[1,2], Yaqi Cui[1,2] and Zhi Wang[1,2]
[1]*School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China*
[2]*Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China*

Study on Infrared Spectrum Detection and Analysis of BTA Residual after Copper CMP (5-16) **348**
Qi Wang[1,2], Baimei Tan[1,2], Siyu Tian[1,2], Chunyu Han[1,2], Liu Yang[1,2] and Baohong Gao[1,2]
[1]*School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China*
[2] *Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China*

Study on the Properties of Nano-Silica Colloid with Mixed Particle Size in Sapphire Substrate CMP (5-20) 351
Weiwei Li, Zhen Liang and Zhilin Zhao
School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China

Effect of Chelating Agent on the Galvanic Corrosion between Copper and Tantalum based Alkaline Polishing Surry (5-22) 354
Jiacheng Qi[1,2], Guofeng Pan[1,2], Chenwei Wang[1,2], Chao Huang[1,2] and Lianjun Hu[1,2]
[1]Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China
[2]School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China

Study on Chemical Mechanical Polishing of R-Plane Sapphire by Different Additives (5-24) 357
Yaqi Cui[1,2], Xinhuan Niu[1,2], Jianchao Wang[1,2], Da Yin[1,2], Jiakai Zhou[1,2] and Zhi Wang[1,2]
[1]School of Electronics and Information Engineering, Hebei University of Technology Tianjin, China
[2]Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China

Effect of Chelation and Oxidation on Reducing Galvanic Corrosion between Cobalt and Copper in Alkaline Slurry (5-25) 360
Chao Huang[1,2], Guofeng Pan[1,2], Jiacheng Qi[1,2] and Chenwei Wang[1,2]
[1]Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China
[2]School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China

Chemical Mechanical Material Removal of Silicon Dioxide by a Single Pad Asperity (5-26) 363
Shuo Yang, Lin Wang, Ping Zhou, Ying Yan and Zhuji Jin
Key Laboratory for Precision and Non-traditional Machining Technology of Ministry of Education, Dalian University of Technology, Dalian, China

Uniformity Improvement and Roughness Reduction by Using Non-Ion Surfactant in the Weakly Alkaline Barrier Slurry (5-29) 366
Cong Wang[1,2], Yuling Liu[1,2], Cheiwei Wang[1,2] and Huihui Zhang[1,2]
[1]School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China
[2]Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China

Potassium Tartrate as a Complexing Agent for Cobalt "Buff Step" CMP in Alkaline Slurry (5-30) 369
Tingwei Liang, Shengli Wang, Chenwei Wang and Fengxia Liu
School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China

Effect of Ammonium Sulfate and H_2O_2 on Cobalt Contact bulk Chemical Mechanical Polishing (5-31) 372
Fengxia Liu[1,2], Shengli Wang[1,2], Chenwei Wang[1,2], Qiyuan Tian[1,2] and Tingwei Liang[1,2]
[1]School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China
[2]Tianjin Key Laboratory of Electronic Materials and Devices, Tianjin, China

Analysis of JFC Adsorption Effect on Surface Roughness of Aluminum for Alkaline CMP by EIS (5-33) 375
Zhi Wang[1,2], Ming Sun[1,2], Xinhuan Niu[1,2], Jiakai Zhou[1,2] and Yaqi Cui[1,2]
[1]Tianjin Key Laboratory of Electronic Materials and Devices, School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China
[2]Institute of Microelectronics, Hebei University of Technology, Tianjin, China

Electrochemical and Surface Analysis of the Chemical Induced Defects with Aluminum Gate CMP (5-35) 378
Ming Sun[1,2] and Zhi Wang[1,2]
[1]School of Electronic Information Engineering, Hebei University of Technology, Tianjin, China
[2]Institute of Microelectronics, Hebei University of Technology, Tianjin, China

The CMP Effect of Potassium Molybdate with BTA as Compound Corrosion Inhibitor used in CMP of the TSV Heterogeneous Microstructure (5-40) 381
Bingquan Wang, Changkun Li, Yuhong Liu and Xinchun Lu
State Key Laboratory of Tribology, Tsinghua University, Haidian District, Beijing, China

REAXFF Molecular Dynamics Simulation of Material Removal Mechanisms During CMP Process of Silica Glass in Aqueous H_2O_2 (5-47) 384
Xiaoguang Guo, Chong Chen, Renke Kang and Zhuji Jin
School of Mechanical Engineering, Dalian University of Technology, Dalian, China

Chapter VI – Metrology, Reliability and Testing

Adjustable Arbiter Physical Unclonable Function with Flexible Response Distribution (6-31) 387
Jing Ye, Xiaowei Li, Huawei Li and Yu Hu
[1]State Key Laboratory of Computer Architecture, Institute of Computing Technology, Chinese Academy of Sciences, Beijing, China
[2]University of Chinese Academy of Sciences, Beijing, China

Quick Development of High Throughput RF Tests on HVM ATE (6-6) 390
Ping Wang, Goh Frank, Haocheng Yuan, Chuansheng Du, Chenpeng Huang and Haixia Guo
Advantest (China) Co., Ltd, Shanghai, China

FPGA Software QoR Benchmarking Methodology Study (6-24) 393
Ping Chen and Shixiao Yan
Lattice Semiconductor (Shanghai) Co., LTD., Shanghai, China

The Cycle Time of Front End IC Manufacturing and AMHS Variability (6-1) 396
George W Horn and William Podgorski
Middlesex Industries SA, Switzerland

Characterization of Laser Recast Profile and Height for Laser Dicing Process (6-26) 399
Yanghua He, Brian Smith and Will Clinton

Process Engineering, Qorvo, Inc., Richardson, Texas, USA

Single Particle Inductivley Coupled Plasma Mass Spectrometry Metrology for Advanced Semiconductor Process Development (6-22) 402
Qilin Chan[1], Waldo Wang[2], Larry Zazzera$_2$, Alex Simpson[2], Jaimie Stomberg[2], Majid Entezarian[3], Daniel Lei[3], Mark Ellefson[4], Brian Mader[4] and Jinsheng Zhou[1]
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[4]3M Company, Corporate Environmental Laboratory, St. Paul, Minnesota, USA

Novel Workflow for High-Resolution Imaging of Structures in Advanced 3D and Fan-Out Packages (6-17) 406
Marcus Kaestner[1], Sascha Mueller[1], Tom Gregorich[2], Cheryl Hartfield[2], Craig Nolen[2] and Ingo Schulmeyer[1]
[1]ZEISS Process Control Solutions, Carl Zeiss SMT GmbH, Oberkochen, Germany
[2]ZEISS Process Control Solutions, Carl Zeiss SMT Inc., Pleasanton, USA

Investigation of Tungsten Rich Residue Defects Induced by Electron Beam Inspection Post Contact Tungsten Chemical and Mechanical Polish (6-5) 409
Rongwei Fan, Hunglin Chen, Kai Wang, Yin Long, Qiliang Ni and Xiaofang Gu
Shanghai Huali Microelectronics Corporation, Shanghai, China

Interaction between Random Telegraph Noise and Hot Carrier Ageing (6-13) 412
A. B. Manut, J. F. Zhang, Z. Ji and W. Zhang
Depart. Electronics and Electrical Engineering, John Moores University, Liverpool, UK

Impact of Hot-Carrier Stress on Oxide Trap Switching Activity in Nanoscale FETs (6-28) 415
Xin Ju and D. S. Ang
School of Electrical and Electronics Engineering, Nanyang Technological University, Singapore

A New Method for Extraction and Analysis of Au Contamination on Semiconductor Wafer Surface (6-12) 418
Mike Ma
Huaying Research Co., Ltd., Wuxi, Jiangsu, China

Practical Exploration of Yield Prediction Model (6-7) 421
Wu Yuan, Xu Yun and Zhang Yuxiang
Shanghai Huahong Grace Semiconductor Manufacture Corporation, Shanghai, China

Highly Sensitive RF Device Setup on ATE (6-10) 424
Haocheng Yuan and Ping Wang
Global Application and Development Center of ADVANTEST, Shanghai, China

A Method for Measuring Resistance of Metal Interconnection Inside Chip (6-14) 427
Chenjie Zhou, Yutian Zhang, Zhimin Zeng, Yun Xu, and Ding Zhou and Xiaotong Ye
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

The Study of Metal Capacitor Transistor TDDB Failure Mechanism (6-18) 430
Chong Huang, Fangce Sun, Ming Zhang and Aiyan Ji

Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

High Efficiency and Low Cost Solution on RFID Tag Measurement (6-33) **432**
Lei Wang
Shanghai Huahong Grace Semiconductor Manufacturing Corporation, Shanghai, China

Chapter VII – Packaging and Assembly

World's First 5G mm-Wave Ultra-Wideband Dual Polarization Antenna using Stackable Packaging - SMARTPOSER™ (7-5) **435**
Cheng Chung Lin[1], Cheng Tar Wu[1], Yen Heng Chen[1], Dirk Zhou[1], Jiao Lv[1], Yuedong Qiu[1], Leslie Huang[1], ZhanYi Qian[2], Bin Yu[2] and Johnson Lin[1]
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[2]Speed Wireless Technology Co., Ltd.,SuZhou City, JiangSu Province, China

Cavity Substrate Technology for SIP Application with Passive Components (7-3) **438**
Ken Lee, Min Sung Kim, Jong Tae Lee, Dong Ju Jeon, Eun Ju Jang and Kyu Jin Lee
Simmtech Co., Ltd., Cheongju, Korea

Redistribution-Layers for Fan-Out Wafer-Level Packaging and Heterogeneous Integrations (7-15)** **443**
John H Lau
ASM Pacific Technology, Hong Kong, China

Studies of the Influence of FOWLP Dimensions on the Flexure Strength (7-7) **453**
C. Xu[1, 2], Z.-W. Zhong[1] and W.-K. Choi[2]
[1]School of Mechanical and Aerospace Engineering, Nanyang Technological University, Singapore
[2]STATS ChipPAC Pte Ltd, Singapore

Advanced Semiconductor Packaging Materials – Copper with Bamboo Structure (7-6) **456**
Jing Wang, Peipei Dong, Xingxing Zhang and Yun Zhang
Suzhou Shinhao Material LLC, Wujiang, Jiangsu, China

Advanced Multifunctional Temporary Bonding Materials with Heterogeneous Integrated Properties for Various Advanced Packaging Applications (7-8) **459**
Xiao Liu, Dongshun Bai, Lisa Kirchner, Rama Puligadda and Tony Flaim
Brewer Science, Inc., Rolla, Missouri, USA

Delamination Improvement for a QFN Package with Stacked Dies by Finite Element Simulation (7-16) **462**
Weidong Huang, Jian Jin, April Yang, Wei Wu, Jacky Wu, Grass Dong and CF Oo
Department of Research and Development, Diodes Shanghai Co., LTD., Shanghai, China

Permanent Bonding Process Development using Gapless Glue for CIS-TSV Wafer Level Packaging (7-13) **465**
Chengqian Wang, Yi Liu, Meng Zhang, Shuying Ma, Zhiyi Xiao and Daquan Yu
HuaTian Technology (Kunshan) Electronics Co., Ltd., Kunshan, Jiangsu Province, China

Optimal Design of Heat Dissipation Structure of IGBT Modules Based on Graphene (7-10) **468**

Hao Zhao[1], Jie Bao[1], Yuan Xu[2] and Wenyi Xu[3]
[1]College of Mechanical and Electrical Engineering, Huangshan University, Huangshan, China
[2]Institute of Semiconductor Technologies and Microsystem, Huangshan University, Huangshan, China
[3]Huangshan Bonnie Two-Dimensional New Material Technology Co., Ltd., Huangshan, China

Wafer Thinning and Dicing Technology for 3D Nand Flash (7-4) **471**
Qian Ma[1], Jiantao Lin[1], Hao Liu[1] and Jeroen van Borkulo[2]
[1]IC Assembly and Test department, Ramaxel Technology Co, Ltd Dongguan, China
[2]ASM Laser Separation International (ALSI) B.V., Netherlands

A Small "Dead-Area" Packaging Approach for Front Side Illuminated Photodiode (7-11) **475**
Wenxuan Cheng, Ru Yang, Jian Liu, Xingan Zhang, Ran He, Kun Liang and Dejun Han
College of Nuclear Science and Technology, Beijing Normal University, Beijing, China

Chapter VIII – MEMS, Sensors and Emerging Semiconductor Technologies

Input Voltage Scheme for DOT Product Engine using NAND Flash Cells (8-20) **478**
Sung-Tae Lee, Suhwan Lim, Nagyong Choi, Jong-Ho Bae, Dongseok Kwon, Hyeong-Su Kim, Byung-Gook Park and Jong-Ho Lee
Department of ECE and ISRC, Seoul National University, Seoul, Korea

The Implementation of Semiconductor Based Biosensors into Point of Need Systems for the Automatized Analysis of Complex Samples* (8-21) **481**
Sascha Geidel, Andreas Morschhauser and Thomas Otto
Fraunhofer Institute for Electronic Nano Systems, Chemnitz, Germany

A High-Sensitivity Low-Noise HDR CMOS Image Sensor Based on Novel 6-TR. 1-CAP. Pixel for Scientific Applications* (8-12) **484**
Chen Li, Jiebin Duan, Xueqiang Gu, Yong Wang, Jianxin Wen, Shoumian Chen, and Yuhang Zhao
Shanghai Integrated Circuits R&D Center Co., Ltd., Shanghai, China

Z^2-FET: A Multi-Functional Device used for Photodetection (8-13) **487**
J. Liu[1], XY. Cao[1], BR. Lu[1], YF. Chen[1], A. Zaslavsky[2], S. Cristoloveanu[3], M. Bawedin[3] and J. Wan[1]
[1]State key lab of ASIC and System, School of Information Science and Technology, Fudan University, Shanghai, China
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[3]IMEP-LAHC, INP-Grenoble/Minatec, Grenoble, France

Batch Atomic Layer Deposition of Aluminum Nitride for RF-MEMS and GaN Power-Devices (8-8) **490**
Zhen Zhu, Erik Østreng, Iiris Tuoriniemi, Zhenzi Chen, Kalle Niiranen and Sami Sneck
Beneq Oy, Espoo, Finland

Numerical Simulation on Filtration Performance of Fibrous Filter Media with Different **493**

Structures (8-4)
Yang Xu[1], Bin Zhou[1] and Lan Zhu[2]
[1]College of Urban Construction, Nanjing Tech University, Nanjing, China
[2]National Air Cleaner & Gas Detect Production Quality Supervision and Inspection Center (Jiangsu), Suzhou, China

Geometry Optimization of Current-Mode Full Symmetric Vertical Hall Device by TCAD Simulation (8-5) **496**
Xingxing Hu[1], Lei Jiang[1], Zixuan Wang[1,2] and Yue Xu[1,2]
[1]College of electronic and optical engineering & College of microelectronics in Nanjing University of Posts and Telecommunications, Nanjing, Jiangsu Province, China
[2]National and Local Joint Engineering Laboratory of RF Integration and Micro-assembly Technology, Nanjing, China

Design of Microbolometer by Polycrystalline Silicon in Standard CMOS Technology (8-22) **499**
Xinwen Cao, Mingcheng Luo, Wei Si, Feng Yan and Xiaoli Ji
Institute of the electronic Science and Engineering, Nanjing University, China

Tube Length Effect of Anodized Aluminum Oxide Template Based Gas Sensor (8-26) **503**
Zhipeng Kang[3], Huayu Hu[3], Xiaojin Zhao[2], Xiaofang Pan[1]
[1]College of Information Engineering, Shenzhen University, Shenzhen, China
[2]College of Electronic Science and Technology, Shenzhen University, Shenzhen, China
[3]College of Optoelectronic Engineering, Shenzhen University, Shenzhen, China

Chapter IX – Design Automation of Circuit and Systems

Efficient Energy Delivery and Dynamic Control for SOC High Power Supply (9-42) **507**
Boping Wu
Huawei Technologies, Shanghai, China

6T&6TPPNN Cell Legalization Considering Complex Minimum Width Constraint (9-38) **510**
Peng Yang[1], Yuhang Chen[1], Jianli Chen[1], Hanbin Zhou[2] and Senhua Dong[2]
[1]Center for Discrete Mathematics and Theoretical Computer Science, Fuzhou University Fuzho, China
[2] Empyrean Software, Inc, Beijing, China

Clock Skew Optimization for Voltage Variation (9-30) **513**
Chung Han Chou[1], Yuan Chao Hsiao[2] and Shih-Chieh Chang[2]
[1]Department of Electronic Engineering, Feng Chia University, China
[2]Department of Computer Science, National Tsing Hua University, China

Not Your Father's Timing Anymore – Novel Approaches to Timing of Digital Circuits (9-7) **516**
Ulf Schlichtmann
Chair of Electronic Design Automation, Technical University of Munich, Munich, Germany

A Low-Computational Complexity System for EEG Signals Compression and Classification (9-14) **520**
Qinming Zhang, Jia Zhang and Cheng Zhuo

College of Information Science & Electronic Engineering, Zhejiang University, Hangzhou, China

An Initial Detailed Routing Algorithm Considering Advanced Technology Nodes (9-39) **523**
Xiqiong Bai[1], Dixiu Xiao[1], Wenxing Zhu[1,2] and Jianli Chen[1,2]
[1]School of Mathematics and Computer Science, Fuzhou University, Fuzhou, China
[2]Center for Discrete Mathematics and Theoretical Computer Science, Fuzhou University, Fuzhou, China

Overview of a FPGA-Based Overlay Processor* (9-6) **526**
Yunxuan Yu[1,2], Chen Wu[1,2], Xiao Shi[2] and Lei He[1,2]
[1]State Key Lab of ASIC and Systems, Fudan University, Shanghai, China
[2]Electric and Computer Engineering Department, UCLA, Los Angeles, CA, USA

A 1μw-to-100μw Output Range Boost DC-DC with Pseudo Open Loop Structure and Power Efficient Ring Oscillator for Wireless Energy Harvesting* (9-27) **529**
Le Ye, Xiaolong Chen, Libo Yang, Hao Zhang, Peiyu Chen, Zhixuan Wang and Enbin Gong
Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronic, Peking University, Beijing, China

A Fast Transient Response Slope-Adjusted Voltage Mode Buck Converter (9-33) **533**
Xu Yang[1], Wanyuan Qu[1], Donglie Gu[1], Haixiao Cao[1], Zhiyuan Tang[1], Jianxiong Xi[1], Lenian He[1] and Shuo Dong[2]
[1]Institute of VLSI Design, Zhejiang University, Hangzhou, China
[2]Shanghai Academy of Spaceflight Technology, Shanghai, China

Efficient FPGA Emulation of Quantum Fourier Transform (9-31) **536**
Yu Qian[1], Mingyu Wang[1], Jialin Chen[1], Lingli Wang[1] and Zhihua Feng[2]
[1]School of Microelectronics, Fudan University, Shanghai, China
[2]Beijing Institute of Computer Technology and Application, Beijing, China

A Low Power 0.4-1 GHz Receiver Front-End with and Enhanced Third-Order-Harmonic-Rejecting Series N-Path Filter (9-37) **539**
Zexue Liu, Heyi Li, Yi Tan, Haoyun Jiang, Junhua Liu and Huailin Liao
Key Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronics, Peking University, Beijing, China

Quality Factors of Ionizing Radiation in CMOS Transistor Gates (9-34) **542**
C.-Z. Chen[1,3], Y. Sun[1,3], David Y. Hu[2] and Hanming Wu[3]
[1]University of Chinese Academy of Sciences, Huairou, Beijing, China
[2]MetroSilicon Microsystems, Kunshan, Jiangsu, China
[3]EtownIP Microelectronics, Beijing, China

Effective Activating Compensation Logic for DRAMS in 3D-ICs (9-18) **545**
Dingcheng Jia and Pingqiang Zhou
School of Information Science and Technology, ShanghaiTech University, Shanghai, China

Inversions Optimization in XOR-Majority Graphs with an Application to QCA (9-17) **548**
Lei Shi and Zhufei Chu
EECS, Ningbo University, Ningbo, China

Area-Power-Delay Trade-Off in Ternary FPRM Circuits Based on MOTLBO **551**

Algorithm (9-23)
Mingbo Wang[1], Pengjun Wang[1,2], Qiang Fu[1,3] and Huihong Zhang[1]
[1]Institute of Circuits And Systems, Ningbo University, Ningbo, China
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[3]College of Science and Technology, Ningbo University, Ningbo, China

Advanced 3D Design Technology Co-Optimization for Manufacturability (9-1) **554**
Yu De Chen, Jacky Huang, Dalong Zhao, Daebin Yi and Joseph Ervin
Coventor Inc., a Lam Research Company, Zuoying Dist., Kaohsiung City, Taiwan

A Sequential Write Scheme for Phase Change Memory Based Serial Interface EEPROM (9-28) **557**
Jui-Jen Wu[1,3], Fan-Yi Jien [1,3], Sheng-Tsai Huang[1,3], Junhua Zheng[2], Peter Xu[2], Mingliang Liao[2], Frank Gao[2], Siyu Nie[2], Chuancong Xiao[2], Gangpeng Zhang[2] and Eric Tsou[1,3]
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[3]Alto Memory Technology Corp.(AMT), Taiwan

A MMIC Ultra-Low Noise Amplifier for S-Band Application (9-11) **560**
Yuchen Wang[1,2], Jiangtao Sun[2], Gaopeng Chen[3] and Dunshan Yu[1]
[1]School of Software and Microelectronics, Peking University, Beijing, China
[2]Highfii Electronic Technology, Beijing, China
[3]Etra Semiconductor, Suzhou, China

A 32-Kb High–Speed 8T SRAM with Fine-Grained Bitline Stacking For Leakage Reduction in 7nm Technology (9-12) **563**
Fei Zhou[1], Xiaoli Hu[2] and Guoxing Wang[1]
[1]Department of Micro-Nano Electronics, Shanghai Jiao Tong University, Shanghai, China
[2]GLOBALFOUNDRIES, Shanghai, China

A Compact SPAD Pixel with Active Quenching and Recharging (9-13) **566**
Jiyuan Lu[1], Bin Li[1], Feng Yuan[1,2] and Yue Xu[1,2]
[1]College of electronic and optical engineering & College of microelectronics in Nanjing University of Posts and Telecommunications, Nanjing, Jiangsu Province, China
[2]National and Local Joint Engineering Laboratory of RF Integration and Micro-Assembly Technology, Nanjing, China

A Novel Compact Time-To-Amplitude Converter For SPAD Detector (9-15) **569**
Zhong Wu[1], Ding Li[1], Feng Yuan[1,2], Xinchun Ji[1,2] and Yue Xu[1,2]
[1] College of electronic and optical engineering & College of microelectronics in Nanjing University of Posts and Telecommunications, Nanjing, Jiangsu Province, China
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A Novel Pseudo-Random Scan Method for Silicon-Based Microdisplay (9-16) **572**
Wendong Chen[1,2], Chunyan Zhang[1], Yuan Ji[1,2], Tingzhou Mu[1] and Feng Ran[1,2]
[1]Microelectronic Research and Development Center, Shanghai University, Shanghai, China
[2]School of Mechatronic Engineering and Automation, Shanghai, China

W-Band LNA for Passive Millimeter Wave Imaging Application (9-19) **575**

Chenxi Liu, Qiannan Ren and Fei Yang
State Key Laboratory of Millimeter Waves, Southeast University, Nanjing, China

An Orthogonal Obfuscation Method on Extend Instruction Sets for Sequrity Risc-V Circuit (9-20) **578**
Jiawei Wang[1], Yuejun Zhang[1,2], Pengjun Wang[1,3], Zhicun Luan[1] and Liwei Li[1]
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[3]College of Physics and Electronic Information Engineering, Wenzhou University, Wenzhou, China

Influence of SiGe On Parasitic Parameters in PMOS (9-21) **581**
Bing Qi Sun[1], Yu De Chen[2], Chen Wang[1], Jacky Huang[2], Qing Qing Sun[1] and David Zhang[1]
[1]School of Microelectronics, Fudan University, Shanghai, China
[2]Coventor Inc., a Lam Research Company, Kaohsiung, Taiwan

A General DTC Nonlinearity Calculation Method for the ADPLL Spur Analysis (9-24) **584**
Xiaoqi Lin, Kanglin Xiao and Bo Wang
The Key Lab of IMS, School of ECE, Peking University, Shenzhen Graduate School, Shenzhen, China

Binary Convolutional Neural Network for Brain Computer Interfaces (9-29) **587**
Shiqi Zhao[1], Xiaoxin Cui[1], Yuanning Fan[1], Chenglong Zou[2] and Dunshan Yu[1]
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[2]School of Electronic and Computer Engineering, Peking University, Shenzhen, China

Hierarchical Quadruplet Net for Deep Metric Learning and Network Regularization (9-32) **590**
Su Zheng[1], Wenqi Tang[1], Zicheng He[1], Jialin Chen[1], Lingli Wang[1], Xuegong Zhou[1] and Zhi-Hua Feng[2]
[1]School of Microelectronics, Fudan University, Shanghai, China
[2]Beijing Institute of Computer Technology and Application, Beijing, China

High-Resolution High-Sensitivity Human-Computer Algorithm and Gesture Control SOC Chip for Artificial Intelligence Applications (9-36) **593**
Chen Li, Tao Zhou, Jianxin Wen and Yuhang Zhao
Shanghai Integrated Circuits R&D Center Co., Ltd., Shanghai, China

NBTI-Aware Digital LDO Design for Edge Devices in IOT Systems (9-40) **596**
Yu-Guang Chen and Yu-Yi Lin
Depart. of Computer Science and Engineering, Yuan Ze University, Taoyuan City, Taiwan

A Low Power Analog Baseband for IoT Applications in 40 nm CMOS (9-43) **599**
Yi Tan, Zexue Liu, Junhua Liu and Huailin Liao
Key Laboratory of Microelectronic Devices and Circuits (MOE), Institute of Microelectronics, Peking University, Beijing, China